



Datasheet

HCA-S-200M-SI

200 MHz Photoreceiver with Si PIN Photodiode



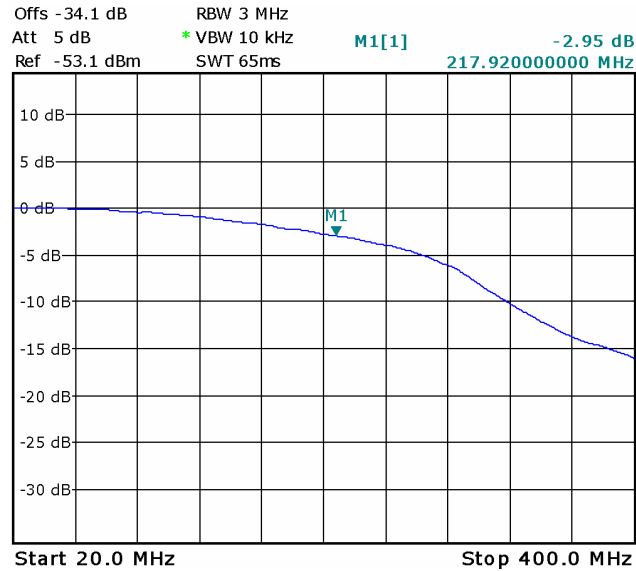
The picture shows the HCA-S-200M-SI-FS with free space input. The photoreceiver will be delivered without post holder and post.

Features	<ul style="list-style-type: none"> • Si PIN Detector, 0.8 mm Active Diameter • Spectral Range 320 ... 1000 nm • Bandwidth DC ... 200 MHz • Amplifier Transimpedance (Gain) 2.0×10^4 V/A • Max. Conversion Gain 1.1×10^4 V/W @ 800 nm 																															
Applications	<ul style="list-style-type: none"> • Spectroscopy • Fast Pulse and Transient Measurements • Optical Triggering • Optical Front-End for Oscilloscopes, A/D Converters and HF Lock-In Amplifiers 																															
Specifications	<table border="0"> <tr> <td></td> <td><i>Test Conditions</i></td> <td><i>V_s = ± 15 V, T_a = 25°C</i></td> </tr> <tr> <td rowspan="2">Gain</td> <td>Transimpedance</td> <td>2.0×10^4 V/A (@ 50 Ω load)</td> </tr> <tr> <td>Max. Conversion Gain</td> <td>1.1×10^4 V/W (@ 800 nm)</td> </tr> <tr> <td rowspan="4">Frequency Response</td> <td>Lower Cut-Off Frequency</td> <td>DC</td> </tr> <tr> <td>Upper Cut-Off Frequency (- 3 dB)</td> <td>200 MHz (± 10 %)</td> </tr> <tr> <td>Rise/Fall Time (10% - 90%)</td> <td>1.8 ns</td> </tr> <tr> <td>Gain Flatness</td> <td>± 1 dB</td> </tr> <tr> <td rowspan="3">Detector</td> <td>Detector Material</td> <td>Si PIN photodiode</td> </tr> <tr> <td>Active Area</td> <td>Ø 0.8 mm</td> </tr> <tr> <td>Spectral Response</td> <td>320 ... 1000 nm</td> </tr> <tr> <td rowspan="3">Input</td> <td>Input Offset Compensation Range</td> <td>± 100 µA adjustable by offset trimpot</td> </tr> <tr> <td>Optical Saturation Power</td> <td>110 µW (for linear amplification, @ 800 nm)</td> </tr> <tr> <td>Min. NEP</td> <td>9.4 pW/√Hz (@ 800 nm, 10 MHz)</td> </tr> </table>		<i>Test Conditions</i>	<i>V_s = ± 15 V, T_a = 25°C</i>	Gain	Transimpedance	2.0×10^4 V/A (@ 50 Ω load)	Max. Conversion Gain	1.1×10^4 V/W (@ 800 nm)	Frequency Response	Lower Cut-Off Frequency	DC	Upper Cut-Off Frequency (- 3 dB)	200 MHz (± 10 %)	Rise/Fall Time (10% - 90%)	1.8 ns	Gain Flatness	± 1 dB	Detector	Detector Material	Si PIN photodiode	Active Area	Ø 0.8 mm	Spectral Response	320 ... 1000 nm	Input	Input Offset Compensation Range	± 100 µA adjustable by offset trimpot	Optical Saturation Power	110 µW (for linear amplification, @ 800 nm)	Min. NEP	9.4 pW/√Hz (@ 800 nm, 10 MHz)
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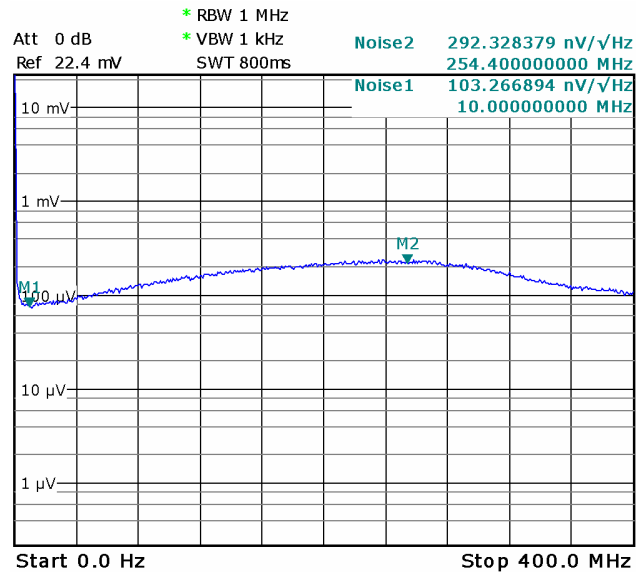
200 MHz Photoreceiver with Si PIN Photodiode

Typical Performance
Characteristics

Frequency Response



Noise Spectrum



Note: Spectral noise data is measured at the amplifier output with no signal on the photodiode. To determine the spectral input noise divide the measured output noise by the amplifier conversion gain.

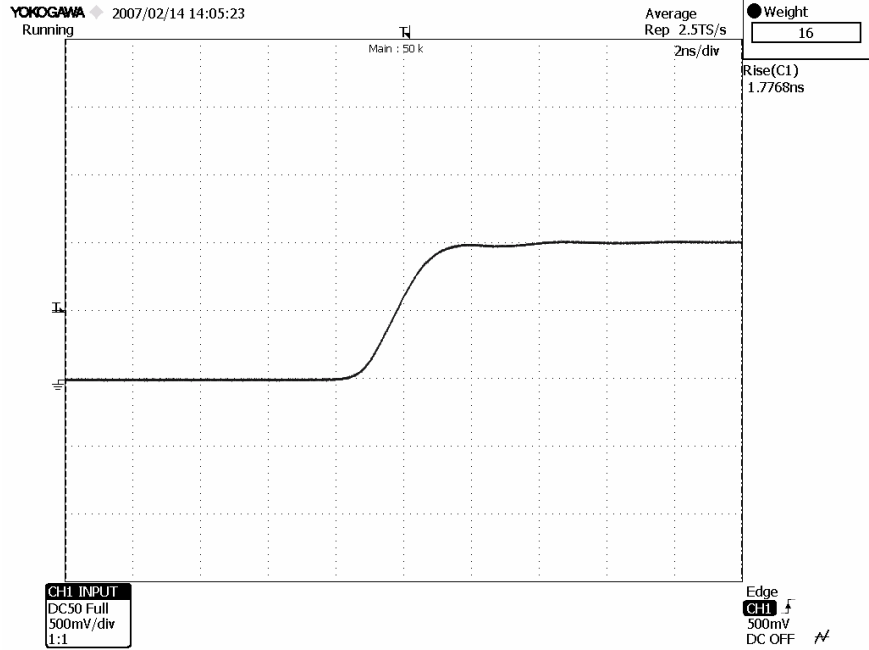
Conversion gain (V/W) = amplifier gain (20,000 V/A) x photo sensitivity (A/W).

Marker	Frequency	Output Noise	Resulting Input Noise (NEP)
1	10 MHz	103 nV/√Hz	9.4 pW/√Hz (@ 800 nm)
2	254 MHz	292 nV/√Hz	27 pW/√Hz (@ 800 nm)

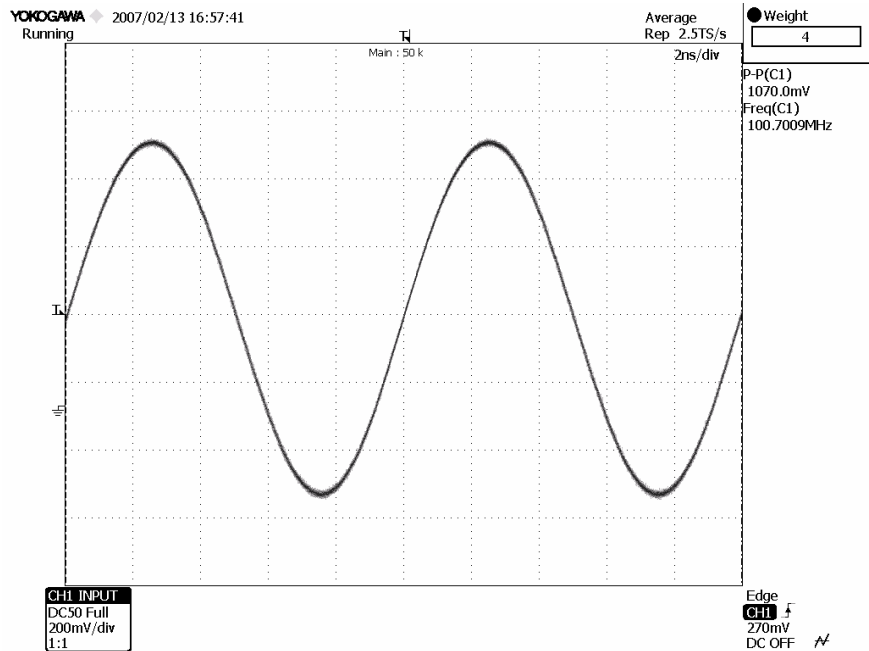
200 MHz Photoreceiver with Si PIN Photodiode

Typical Performance Characteristics (continued)

Pulse Response to Square Wave Input Signal (with 16 times averaging)



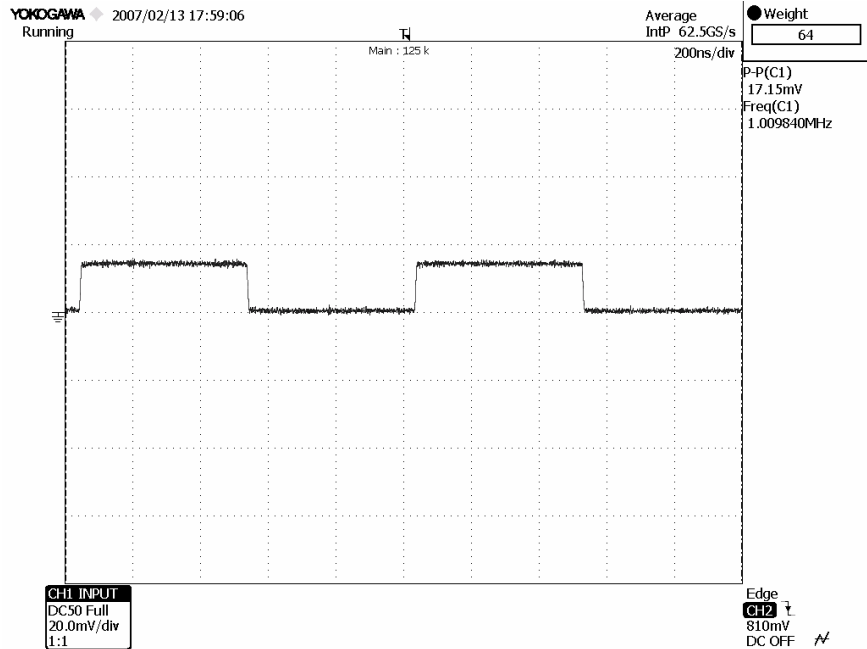
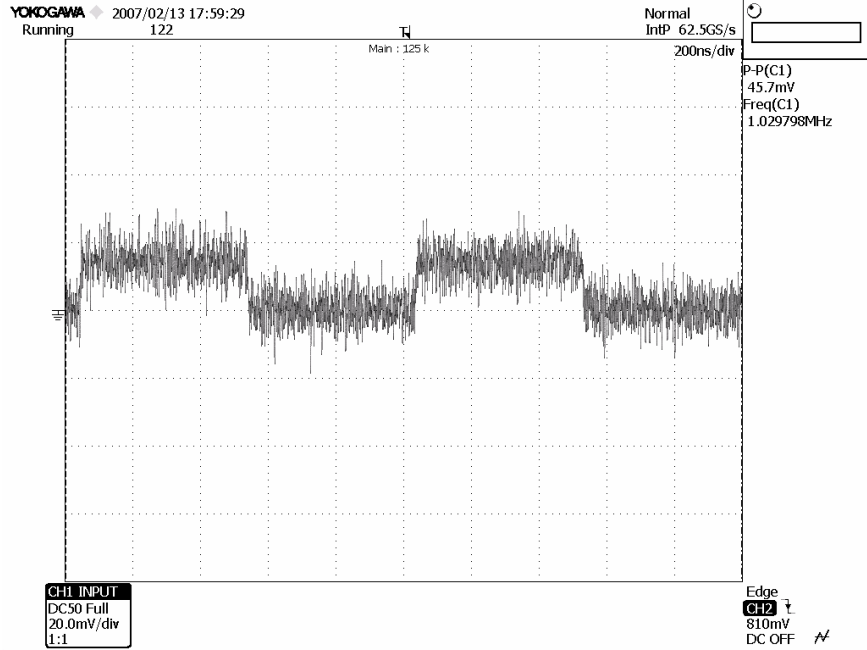
Large Signal Response output signal for 100 MHz, 100 μ W modulated optical input signal (with 4 times averaging)



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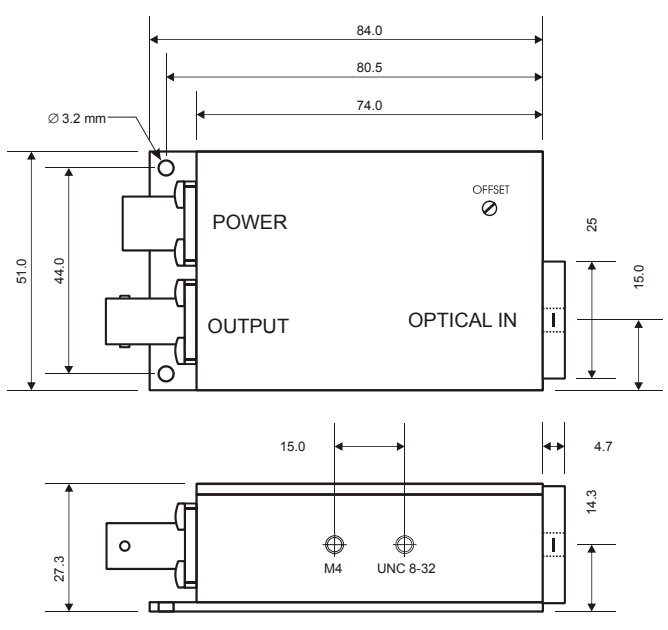
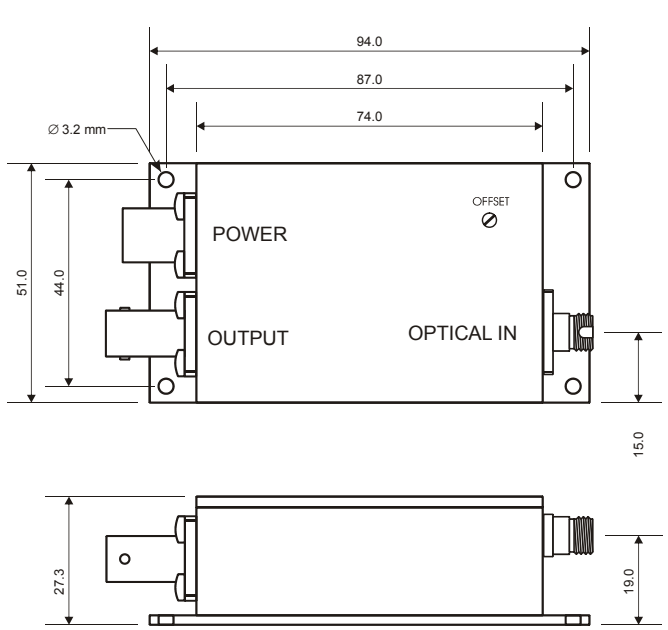
Typical Performance Characteristics (continued)

Small Signal Response
output signal for 1.5 μ W modulated optical input signal, 1 MHz square wave (without (top) and with 64 times averaging (bottom))



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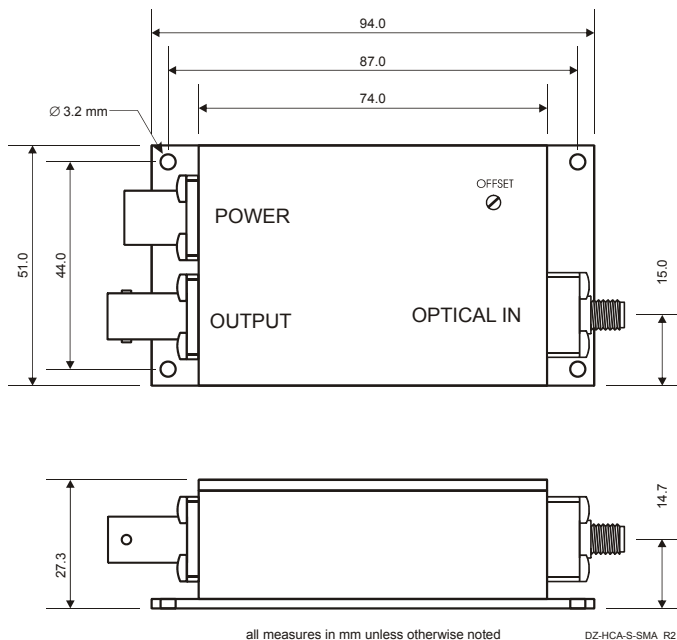
Available Models	<p>HCA-S-200M-SI-FS free space input HCA-S-200M-SI-FC FC fiber optic receptacle HCA-S-200M-SI-SMA SMA fiber optic receptacle HCA-S customized versions available on request</p>
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Dimensions	<p>HCA-S-200M-SI-FS</p>  <p>all measures in mm unless otherwise noted DZ-HCA-S-FS_R2</p> <p>HCA-S-200M-SI-FC</p>  <p>all measures in mm unless otherwise noted DZ-HCA-S-FC_R4</p>
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200 MHz Photoreceiver with Si PIN Photodiode

Dimensions (continued)

HCA-S-200M-SI-SMA



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